

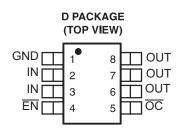


SINGLE-CHANNEL 100 mA POWER SWITCH

FEATURES

- 100-mA Continuous Current
- 600-mΩ High-Side MOSFET
- Thermal and Short-Circuit Protection
- Operating Range: 2.7 V to 5.5 V
- 0.6-ms Typical Rise Time
- Undervoltage Lockout
- Deglitched Fault Report (OC)
- 43 µA Quiescent Supply Current
- 1-µA Maximum Standby Supply Current

- SOIC-8 Package
- Ambient Temperature Range: -40°C to 85°C
- 2 µS Response Time to Short Circuit



DESCRIPTION

The TPS2049 power-distribution switch is intended for applications where heavy capacitive loads and short circuits are likely to be encountered. This device incorporates a 600-m Ω N-channel MOSFET power switch for power-distribution systems that require only one power distribution path. The switch is controlled by a logic enable input. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7V.

When the output load exceeds the current-limit threshold or a short is present, the device limits the output current to a safe level by switching into a constant-current mode, pulling the overcurrent (\overline{OC}) logic output low. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures the switch remains off until valid input voltage is present. This power-distribution switch is designed to set current limit at 150mA typically.

GENERAL SWITCH CATALOG							
33 mΩ single TPS201xA 0.2 A - 2 A TPS202x 0.2 A - 2 A TPS203x 0.2 A - 2 A	80 mΩ, single TPS2014 600 mA TPS2015 1A TPS2045 500 mA TPS2045A 250 mA TPS2055A 250 mA TPS2061 1A TPS2065 1A TPS2065 1A TPS2068 1.5 A	80 mΩ, dual TPS2042B 500 mA TPS2052B 500 mA TPS2056 250 mA TPS2056 250 mA TPS2066 1 A TPS2066 1 A TPS2060 1.5 A TPS2064 1.5 A	80 mΩ, dual TPS2080 500 mA TPS2081 500 mA TPS2082 500 mA TPS2090 250 mA TPS2091 250 mA TPS2092 250 mA	80 mΩ, triple TPS2043B 500 mA TPS2043B 500 mA TPS2053B 500 mA TPS2057A 250 mA TPS2063 1 A TPS2067 1 A	80 mΩ, quad	80 mΩ, quad 0 0 0 0 0 0 0 0	



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTION AND ORDERING INFORMATION⁽¹⁾

T _A	ENABLE	RECOMMENDED MAXIMUM CONTINUOUS LOAD CURRENT (mA)	TYPICAL SHORT-CIRCUIT CURRENT LIMIT AT 25°C (mA)	NUMBER OF SWITCHES	SOIC (D)
–40°C to 85°C	Active low	100	150	Single	TPS2049D ⁽²⁾

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(2) The package is available taped and reeled. Add an R suffix to device types (e.g., TPS2042BDR)

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted⁽¹⁾

			VALUE	UNIT	
V _{I(IN)}	Input voltage range (2)		-0.3 to 6	V	
V _{O(OUT)}	Output voltage range (2)	-0.3 to 6	V		
V _{I(EN)}	Input voltage range	Input voltage range			
V _{I(OC)}	Voltage range		–0.3 to 6	V	
I _{O(OUT)}	Continuous output current	Internally lim	Internally limited		
	Continuous total power dissipati	on	See Dissipation Ra	ting Table	
TJ	Operating virtual junction tempe	rature range	-40 to 125	°C	
T _{stg}	Storage temperature range		-65 to 150	°C	
	Lead temperature soldering 1,6	mm (1/16 inch) from case for 10 seconds	260	°C	
	Electrostatic discharge (ESD)	Human body model MIL-STD-883C	2	kV	
	protection	Charge device model (CDM)	500	V	

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to GND.

DISSIPATING RATING TABLE

PACKAGE	T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
D-8	585.82 mW	5.8582 mW/C	322.20 mW	234.32 mW

RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNIT
V _{I(IN)}	Input voltage	2.7	5.5	V
V _{I(EN)}	Input voltage	0	5.5	V
I _{O(OUT)}	Continuous output current	0	100	mA
TJ	Operating virtual junction temperature	-40	125	°C



ELECTRICAL CHARACTERISTICS

over recommended operating junction temperature range, $V_{I(IN)} = 5.5 \text{ V}$, $I_O = 90 \text{ mA}$, $V_{I(EN)} = 0 \text{ V}$ (unless otherwise noted)

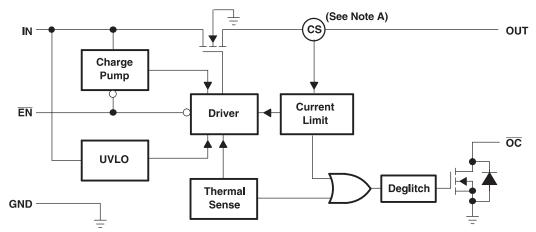
	PARAMETER	-	MIN	TYP	MAX	UNIT		
POWEF	R SWITCH	·						
r _{DS(on)}	Static drain-source on-state resistance, 5-V operation and 2.7-V operation	$V_{I(IN)} = 2.7 V \text{ or } 5.5 V,$	I _O = 90 A,	–40°C < T _J < 125°C		400	650	mΩ
t _r	Rise time, output	V _{I(IN)} = 2.7 V	$C_{L} = 1 F,$	$R_L = 50 \ \Omega, \ T_J = 25^{\circ}C$		0.1	0.4	ms
t _f	Fall time, output	V _{I(IN)} = 2.7 V	$C_{L} = 1 F,$	$R_L = 50 \ \Omega, \ T_J = 25^{\circ}C$	0.03		0.3	ms
ENABL	e input <u>en</u>							
V _{IH}	High-level input voltage	$2.7 \text{ V} \leq \text{V}_{I(IN)} \leq 5.5 \text{ V}$			2			V
V _{IL}	Low-level input voltage	$2.7 \text{ V} \leq \text{V}_{I(IN)} \leq 5.5 \text{ V}$					0.8	V
l _l	Input current	$V_{I(EN)} = 0 V \text{ or } V_{I(EN)} = V$	V _{I(IN)}		-0.5		0.5	μA
t _{on}	Turnon time	$C_L = 1 \ \mu F, R_L = 50 \ \Omega, T$	∫ _J = 25°C				1	ms
t _{off}	Turnoff time	$C_L = 1$ F, $R_L = 50$ Ω , T_J	= 25°C				1	ms
CURRE								
I _{OS}	Short-circuit output current	$V_{I(IN)} = 5 V$, OUT conne short-circuit, $10^{\circ}C < T_J$	$V_{I(IN)} = 5 \text{ V}$, OUT connected to GND, Device enabled into short-circuit, $10^{\circ}C < T_J < 40^{\circ}C$				200	mA
I _{OC_trip}	Overcurrent trip threshold	$10^{\circ}C < T_{J} < 40^{\circ}C, 100$	A/sec current rate i	ncrease	3			
	Short-circuit response time					2		μs
SUPPL	Y CURRENT							
				$T_J = 25^{\circ}C$	0.5 1		1	
Supply	current, low-level output	No load on OUT	V _{I(EN)} = 5.5 V	–40C ≤ T _J ≤ 125°C		0.5	5	μA
Supply	ourrent high lovel output	No load on OUT	$\gamma = 0 \gamma$	$T_J = 25^{\circ}C$		43	60	۵
Supply	current, high-level output	NO IDAU ON OUT	$V_{I(EN)} = 0 V$	$-40C \le T_J \le 125^{\circ}C$		43	70	μA
Leakage	e current	OUT connected to ground	$V_{I(EN)} = 5.5 V,$	–40C ≤ T _J ≤ 125°C		1		А
Reverse	e leakage current	IN = ground		$T_J = 25^{\circ}C$		0		μA
UNDER	VOLTAGE LOCKOUT							
IN	Low-level input voltage				2		2.5	V
IN	Hysteresis	T _J = 25C				75		mV
OVERC	URRENT OC							
V _{OL(OC)}	Output low voltage	$I_{O(OC)} = 5 \text{ mA}$					0.4	V
Off-state	e current	$V_{O(\overline{OC})} = 5 \text{ V or } 3.3 \text{ V}$					1	μA
OC deg		OC assertion or de-ass	ertion		4	8	15	ms
THERM	IAL SHUTDOWN ⁽²⁾							
Therma	I shutdown threshold				135			°C
Recove	ry from thermal shutdown				125			°C
Hystere	sis					10		°C

(1) Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

(2) The thermal shutdown only reacts under overcurrent conditions.





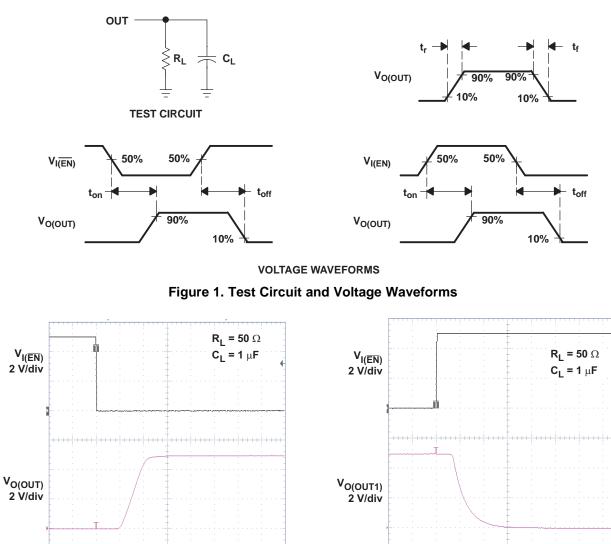


Note A: Current sense

TERMINAL FUNCTIONS

TE	TERMINAL		DESCRIPTION
NAME	NO.	I/O	DESCRIPTION
EN1	4	I	Enable input, logic low turns on power switch
GND	1	I	Ground
IN	2, 3	I	Input voltage
<u> 00</u>	5	0	Overcurrent, report, active-low, open-drain output
OUT	6, 7, 8	0	Power-switch output

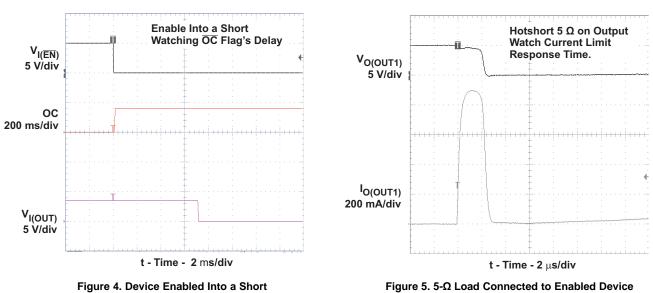
PARAMETER MEASUREMENT INFORMATION



t - Time - 100 $\mu s/div$ Figure 2. Turnon Delay and Rise Time With 1- μF Load

Figure 3. Turnoff Delay and Fall Time With 1- μF Load

t - Time - 100 μs/div



PARAMETER MEASUREMENT INFORMATION (continued)



APPLICATION INFORMATION

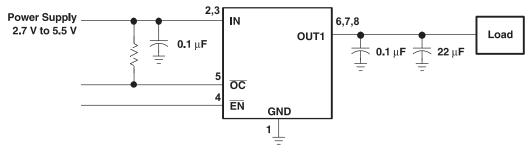


Figure 6. Typical Application

POWER-SUPPLY CONSIDERATIONS

A $0.01-\mu$ F to $0.1-\mu$ F ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a $0.01-\mu$ F to $0.1-\mu$ F ceramic capacitor improves the immunity of the device to short-circuit transients.

OVERCURRENT

A sense FET is employed to check for overcurrent conditions. Unlike current–sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before VI(IN) has been applied (see Figure 6). The TPS2049 senses the short and immediately switches into a constant-current output.

In the second condition, a short or an overload occurs while the device is enabled. At the instant the overload occurs, very high currents may flow for a short period of time before the current-limit circuit can react. After the current-limit circuit has tripped (reached the overcurrent trip threshold) the device switches into constant-current mode.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached or until the thermal limit of the device is exceeded. The TPS2049 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its constant-current mode.

OC RESPONSE

The $\overline{\text{OC}}$ open-drain output is asserted (active low) when an overcurrent or overtemperature shutdown condition is encountered after a 10-ms deglitch timeout. The output remains asserted until the overcurrent or overtemperature condition is removed. Connecting a heavy capacitive load to an enabled device can cause a momentary overcurrent condition; however, no false reporting on $\overline{\text{OC}}$ occurs due to the 10-ms deglitch circuit. The TPS2049 is designed to eliminate false overcurrent reporting. The internal overcurrent deglitch eliminates the need for external components to remove unwanted pulses. $\overline{\text{OC}}$ is not deglitched when the switch is turned off due to an overtemperature shutdown.

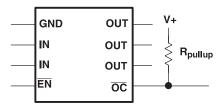


Figure 7. Typical Circuit for the OC Pin



POWER DISSIPATION AND JUNCTION TEMPERATURE

The low on-resistance on the n-channel MOSFET allows small surface-mount packages to pass large currents. The thermal resistance of these packages are high compared to those of power packages; it is good design practice to check power dissipation and junction temperature. Begin by determining the r_{DS(on)} of the N-channel MOSFET relative to the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest. Using this value, the power dissipation per switch can be calculated by:

 $P_D = r_{DS(on)} \times I^2$

Finally, calculate the junction temperature:

 $T_J = P_D \times R_{\Theta JA} + T_A$

Where:

 T_A = Ambient temperature °C

 $R_{\Theta JA}$ = Thermal resistance

 P_D = Total power dissipation based on number of switches being used.

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation, using the calculated value as the new estimate. Two or three iterations are generally sufficient to get a reasonable answer.

THERMAL PROTECTION

Thermal protection prevents damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The TPS2049 implement a thermal sensing to monitor the operating junction temperature of the power distribution switch. In an overcurrent or short-circuit condition the junction temperature will rise due to excessive power dissipation. Once the die temperature rises to approximately 140°C due to overcurrent conditions, the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit, and after the device has cooled approximately 10°C, the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The OC open-drain output is asserted (active low) when an overtemperature shutdown or overcurrent occurs.

UNDERVOLTAGE LOCKOUT (UVLO)

An undervoltage lockout ensures that the power switch is in the off state at power up. Whenever the input voltage falls below approximately 2 V, the power switch will be quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed. The UVLO will also keep the switch from being turned on until the power supply has reached at least 2 V, even if the switch is enabled. Upon reinsertion, the power switch will be turned on, with a controlled rise time to reduce EMI and voltage overshoots.



GENERIC HOT-PLUG APPLICATIONS (see Figure 8)

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the TPS2049, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the TPS2049 also ensures the switch will be off after the card has been removed, and the switch will be off during the next insertion. The UVLO feature insures a soft start with a controlled rise time for every insertion of the card or module.

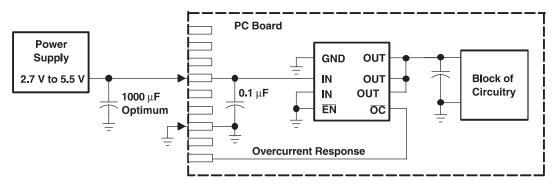


Figure 8. Typical Hot-Plug Implementation

By placing the TPS2049 between the V_{CC} input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1 ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge currents and provides a hot-plugging mechanism for any device.

DETAILED DESCRIPTION

POWER SWITCH

The power switch is an N-channel MOSFET with a low on-state resistance. Configured as a high-side switch, the power switch prevents current flow from OUT to IN and IN to OUT when disabled. The power switch supplies a minimum current of 90 mA.

CHARGE PUMP

An internal charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires little supply current.

DRIVER

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage.

ENABLE (EN)

The logic enable pin disables the power switch and the bias for the charge pump, driver, and other circuitry to reduce the supply current. The supply current is reduced to less than 1 μ A when a logic high is present on EN. A logic zero input on EN restores bias to the drive and control circuits and turns the switch on. The enable input is compatible with both TTL and CMOS logic levels.



OVERCURRENT (OC)

The \overline{OC} open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output remains asserted until the overcurrent or overtemperature condition is removed. A 10-ms deglitch circuit prevents the \overline{OC} signal from oscillation or false triggering. If an overtemperature shutdown occurs, the \overline{OC} is asserted instantaneously.

CURRENT SENSE

A sense FET monitors the current supplied to the load. The sense FET measures current more efficiently than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver in turn reduces the gate voltage and drives the power FET into its saturation region, which switches the output into a constant-current mode and holds the current constant while varying the voltage on the load.

THERMAL SENSE

The TPS2049 implements a thermal sensing to monitor the operating temperature of the power distribution switch. In an overcurrent or short-circuit condition, the junction temperature rises. When the die temperature rises to approximately 140°C due to overcurrent conditions, the internal thermal sense circuitry turns off the switch, thus preventing the device from damage. Hysteresis is built into the thermal sense, and after the device has cooled approximately 10 degrees, the switch turns back on. The switch continues to cycle off and on until the fault is removed. The open-drain false reporting output (\overline{OC}) is asserted (active low) when an overtemperature shutdown or overcurrent occurs.

UNDERVOLTAGE LOCKOUT

A voltage sense circuit monitors the input voltage. When the input voltage is below approximately 2V, a control signal turns off the power switch.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS2049D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2049DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2049DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2049DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

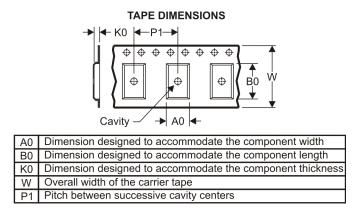
Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TEXAS INSTRUMENTS www.ti.com

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



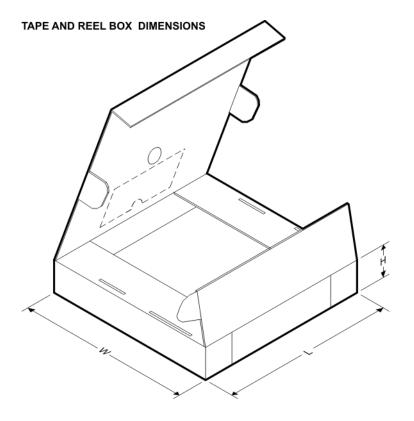
*All dimensions a	are nominal
-------------------	-------------

Device		Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2049DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

19-Mar-2008

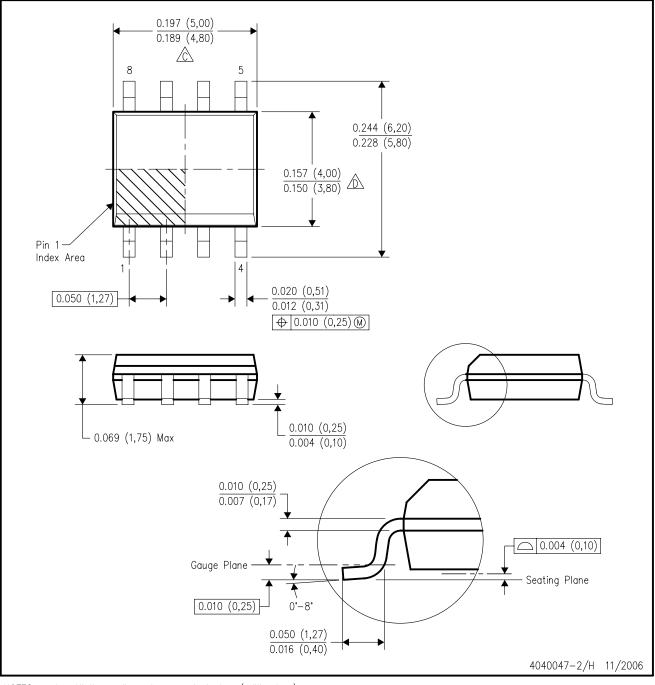


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2049DR	SOIC	D	8	2500	340.5	338.1	20.6

D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.

Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.

E. Reference JEDEC MS-012 variation AA.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Clocks and Timers	www.ti.com/clocks	Digital Control	www.ti.com/digitalcontrol
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
RFID	www.ti-rfid.com	Telephony	www.ti.com/telephony
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2008, Texas Instruments Incorporated